

Doped 4N Copper Wire for Bonding in Microelectronics Device

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ABSTRACT

A doped 4N copper wire for bonding in microelectronics comprising one or more of a group of Ag, Ni, Pd, Au, Pt, and Cr as corrosion resistance dopant material, wherein a concentration of said corrosion resistance dopant material is between about 10wt.ppm and about 80wt.ppm.

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FIG. 1

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